

Lonten N-channel 600V, 47A, 0.07Ω LonFET™ Power MOSFET

| | | | | | | | | | |
|--|--|----------------------|------|------------------|-------|----------|------|-------------|------|
| <p>Description LonFET™ Power MOSFET is fabricated using advanced super junction technology. The resulting device has extremely low on resistance, making it especially suitable for applications which require superior power density and outstanding efficiency.</p> <p>Features</p> <ul style="list-style-type: none"> ◆ Ultra low $R_{DS(on)}$ ◆ Ultra low gate charge (typ. $Q_g = 68\text{nC}$) ◆ 100% UIS tested ◆ RoHS compliant <p>Applications</p> <ul style="list-style-type: none"> ◆ Power factor correction (PFC). ◆ Switched mode power supplies (SMPS). ◆ Uninterruptible power supply (UPS). | <p>Product Summary</p> <table style="width: 100%; border: none;"> <tr> <td style="padding: 2px;">$V_{DS} @ T_{j,max}$</td> <td style="padding: 2px;">650V</td> </tr> <tr> <td style="padding: 2px;">$R_{DS(on),max}$</td> <td style="padding: 2px;">0.07Ω</td> </tr> <tr> <td style="padding: 2px;">I_{DM}</td> <td style="padding: 2px;">141A</td> </tr> <tr> <td style="padding: 2px;">$Q_{g,typ}$</td> <td style="padding: 2px;">68nC</td> </tr> </table> <div style="text-align: center; margin-top: 10px;"> </div> <p style="text-align: center; margin-top: 10px;">N-Channel MOSFET</p> | $V_{DS} @ T_{j,max}$ | 650V | $R_{DS(on),max}$ | 0.07Ω | I_{DM} | 141A | $Q_{g,typ}$ | 68nC |
| $V_{DS} @ T_{j,max}$ | 650V | | | | | | | | |
| $R_{DS(on),max}$ | 0.07Ω | | | | | | | | |
| I_{DM} | 141A | | | | | | | | |
| $Q_{g,typ}$ | 68nC | | | | | | | | |

Absolute Maximum Ratings

| Parameter | Symbol | Value | Unit |
|--|----------------|-------------|---------------------|
| Drain-Source Voltage | V_{DSS} | 600 | V |
| Continuous drain current ($T_C = 25^\circ\text{C}$) | I_D | 47 | A |
| ($T_C = 100^\circ\text{C}$) | | 30 | A |
| Pulsed drain current ¹⁾ | I_{DM} | 141 | A |
| Gate-Source voltage | V_{GSS} | ± 30 | V |
| Avalanche energy, single pulse ²⁾ | E_{AS} | 1055 | mJ |
| Power Dissipation TO-247 ($T_C = 25^\circ\text{C}$) | P_D | 280 | W |
| - Derate above 25°C | | 2.24 | W/ $^\circ\text{C}$ |
| Power Dissipation TO-220MF ($T_C = 25^\circ\text{C}$) | P_D | 37 | W |
| - Derate above 25°C | | 0.30 | W/ $^\circ\text{C}$ |
| Operating and Storage Temperature Range | T_J, T_{STG} | -55 to +150 | $^\circ\text{C}$ |
| Continuous diode forward current | I_S | 47 | A |
| Diode pulse current | $I_{S,pulse}$ | 141 | A |

Thermal Characteristics TO-247

| Parameter | Symbol | Value | Unit |
|---|-----------------|-------|---------------|
| Thermal Resistance, Junction-to-Case | $R_{\theta JC}$ | 0.45 | $^{\circ}C/W$ |
| Thermal Resistance, Junction-to-Ambient | $R_{\theta JA}$ | 62 | $^{\circ}C/W$ |
| Soldering temperature, wavesoldering only allowed at leads. (1.6mm from case for 10s) | T_{sold} | 260 | $^{\circ}C$ |

Thermal Characteristics TO-220MF

| Parameter | Symbol | Value | Unit |
|---|-----------------|-------|---------------|
| Thermal Resistance, Junction-to-Case | $R_{\theta JC}$ | 3.33 | $^{\circ}C/W$ |
| Thermal Resistance, Junction-to-Ambient | $R_{\theta JA}$ | 77 | $^{\circ}C/W$ |
| Soldering temperature, wavesoldering only allowed at leads. (1.6mm from case for 10s) | T_{sold} | 260 | $^{\circ}C$ |

Package Marking and Ordering Information

| Device | Device Package | Marking | Units/Tube | Units/Reel |
|-------------|----------------|-------------|------------|------------|
| LSB60R070HT | TO-247 | LSB60R070HT | 30 | |
| LSD60R070HT | TO-220MF | LSD60R070HT | 50 | |

Electrical Characteristics $T_c = 25^{\circ}C$ unless otherwise noted

| Parameter | Symbol | Test Condition | Min. | Typ. | Max. | Unit |
|------------------------------------|--------------|--|------|-------|-------|----------|
| Static characteristics | | | | | | |
| Drain-source breakdown voltage | BV_{DSS} | $V_{GS}=0V, I_D=0.25mA$ | 600 | - | - | V |
| Gate threshold voltage | $V_{GS(th)}$ | $V_{DS}=V_{GS}, I_D=0.25mA$ | 2.5 | 3.5 | 4.5 | V |
| Drain cut-off current | I_{DSS} | $V_{DS}=600V, V_{GS}=0V,$ $T_j = 25^{\circ}C$ $T_j = 125^{\circ}C$ | - | - | 1 | μA |
| | | | - | 10 | - | |
| Gate leakage current, Forward | I_{GSSF} | $V_{GS}=30V, V_{DS}=0V$ | - | - | 100 | nA |
| Gate leakage current, Reverse | I_{GSSR} | $V_{GS}=-30V, V_{DS}=0V$ | - | - | -100 | nA |
| Drain-source on-state resistance | $R_{DS(on)}$ | $V_{GS}=10V, I_D=23.5A$ $T_j = 25^{\circ}C$ $T_j = 150^{\circ}C$ | - | - | - | Ω |
| | | | - | 0.060 | 0.070 | |
| | | | - | 0.16 | - | |
| Dynamic characteristics | | | | | | |
| Input capacitance | C_{iss} | $V_{DS} = 100V, V_{GS} = 0V,$ $f = 250kHz$ | - | 4070 | - | pF |
| Output capacitance | C_{oss} | | - | 158 | - | |
| Reverse transfer capacitance | C_{rss} | | - | 2.5 | - | |
| Turn-on delay time | $t_{d(on)}$ | $V_{DD} = 400V, I_D = 23.5A$ $R_G = 10\Omega, V_{GS}=10V$ | - | 32.3 | - | ns |
| Rise time | t_r | | - | 66.2 | - | |
| Turn-off delay time | $t_{d(off)}$ | | - | 200 | - | |
| Fall time | t_f | | - | 11.7 | - | |
| Gate charge characteristics | | | | | | |
| Gate to source charge | Q_{gs} | $V_{DD}=480V, I_D=23.5A,$ | - | 19.1 | - | |

| | | | | | | |
|--------------------------------------|---------------|---|---|------|---|---------|
| Gate to drain charge | Q_{gd} | $V_{GS}=0$ to 10 V | - | 19.2 | - | nC |
| Gate charge total | Q_g | | - | 68 | - | |
| Gate plateau voltage | $V_{plateau}$ | | - | 5.0 | - | V |
| Reverse diode characteristics | | | | | | |
| Diode forward voltage | V_{SD} | $V_{GS}=0$ V, $I_F=23.5$ A | - | 1.0 | - | V |
| Reverse recovery time | t_{rr} | $V_R=50$ V, $I_F=20$ A, $di_F/dt=100$ A/ μ s | - | 415 | - | ns |
| Reverse recovery charge | Q_{rr} | | - | 4.9 | - | μ C |
| Peak reverse recovery current | I_{rrm} | | - | 23.8 | - | A |

Notes:

- Limited by maximum junction temperature, maximum duty cycle is 0.75.
- $I_{AS} = 7.5$ A, $V_{DD} = 60$ V, Starting $T_J = 25^\circ$ C.

Electrical Characteristics Diagrams

Figure 1. On-Region Characteristics

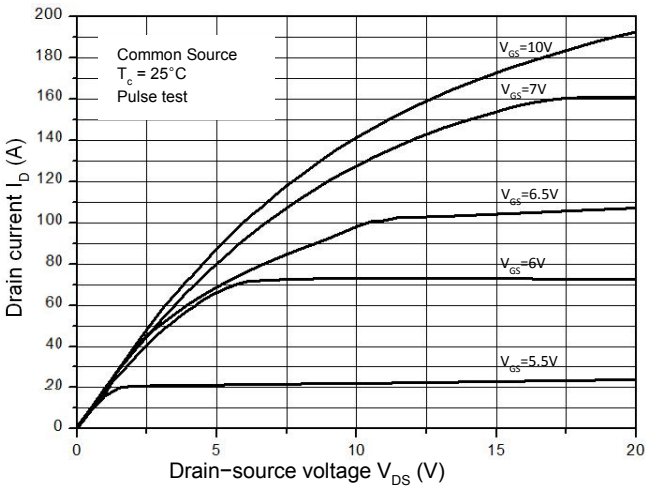


Figure 2. Transfer Characteristics

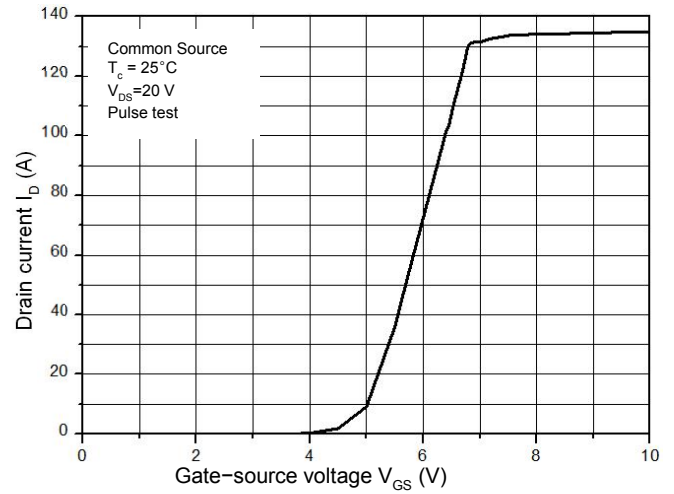


Figure 3. On-Resistance Variation vs. Drain Current

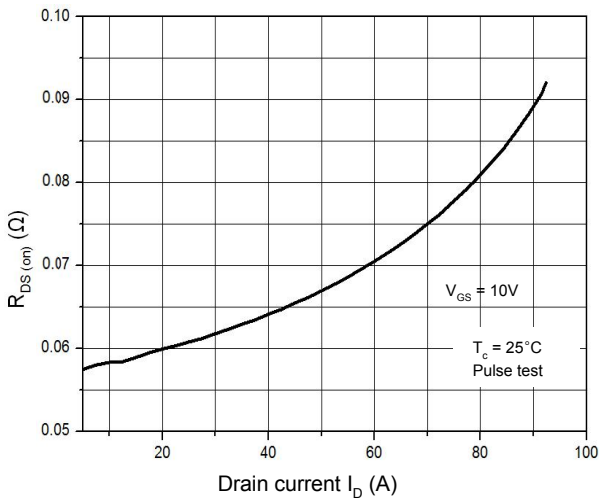


Figure 4. Threshold Voltage vs. Temperature

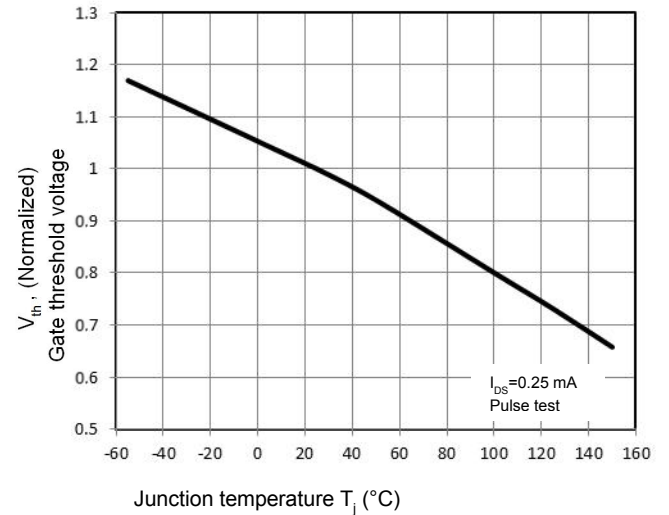


Figure 5. Breakdown Voltage vs. Temperature

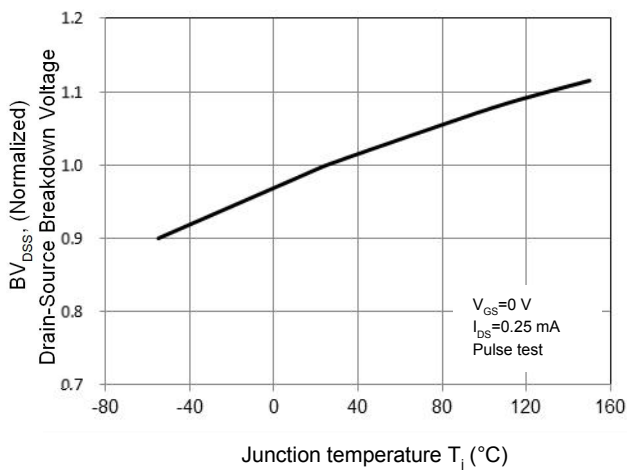


Figure 6. On-Resistance vs. Temperature

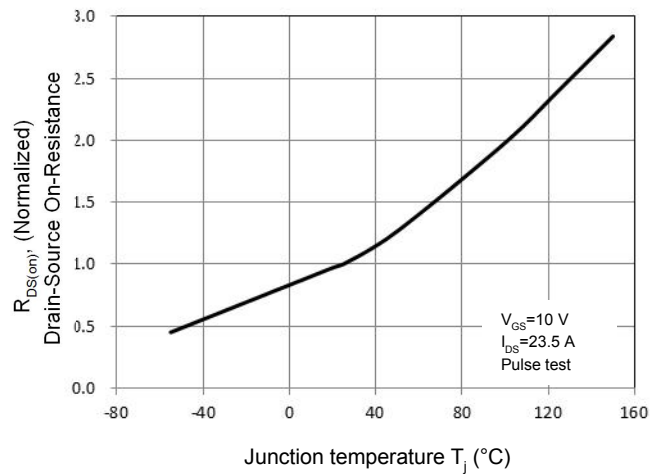


Figure 7. Capacitance Characteristics

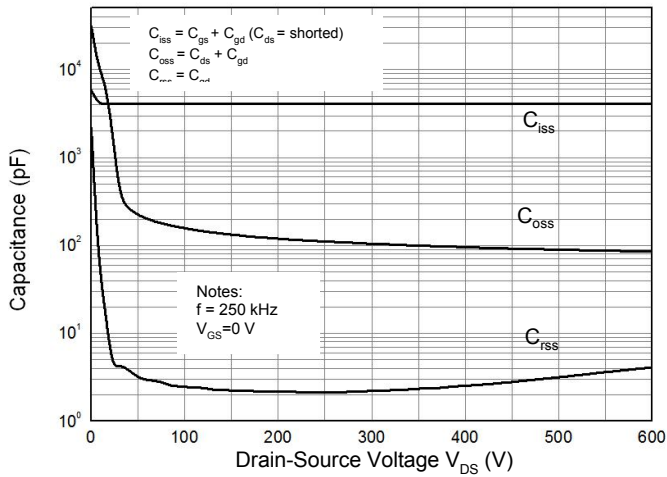


Figure 8. Gate Charge Characterist

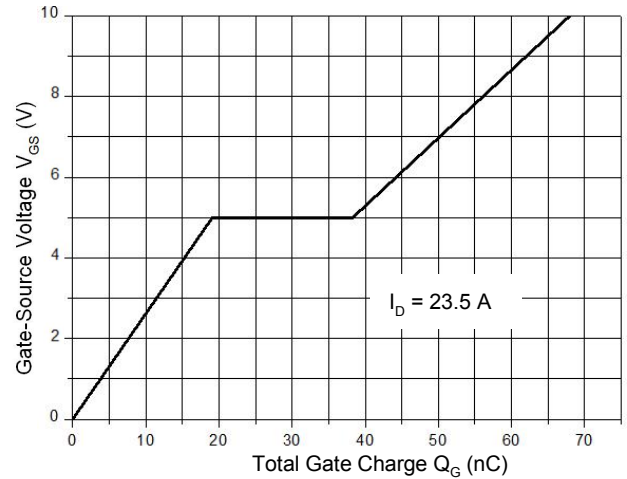


Figure 9.1 Maximum Safe Operating Area
TO-247

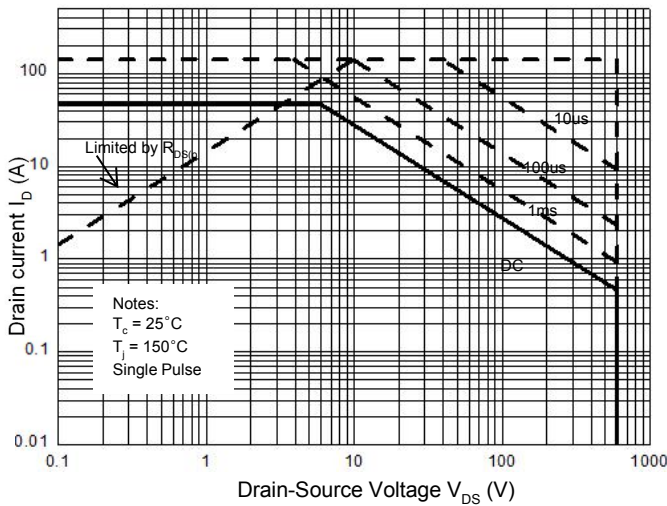


Figure 9.2 Maximum Safe Operating Area
TO-220MF

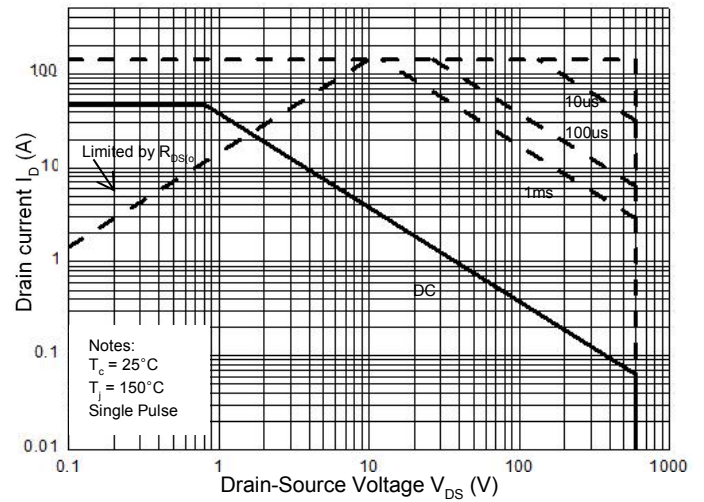


Figure 10.1 Power Dissipation vs. Temperature
TO-247

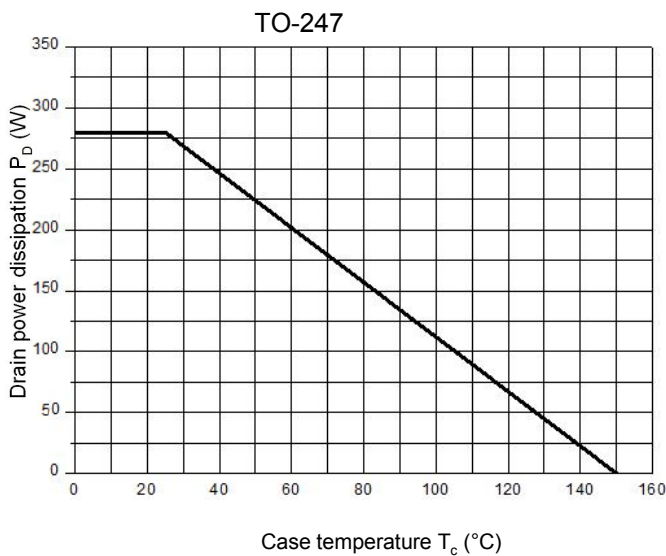
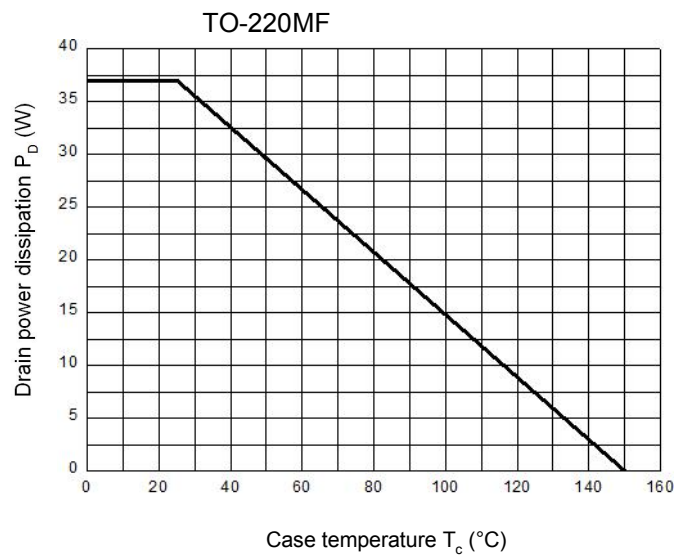
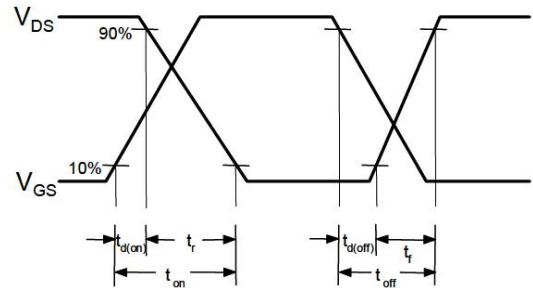
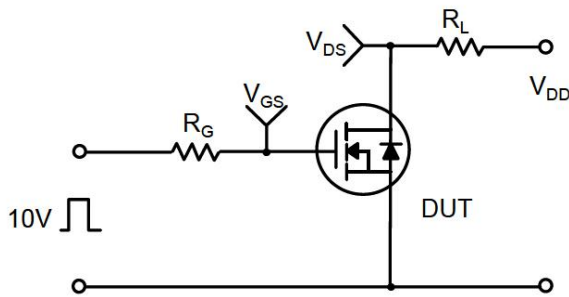
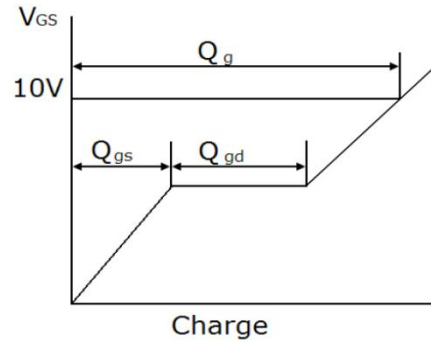
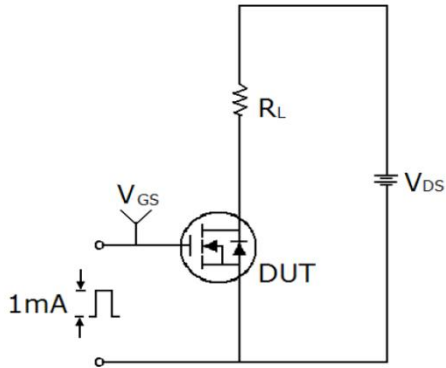


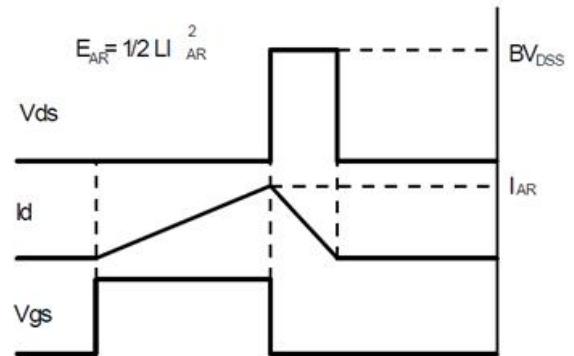
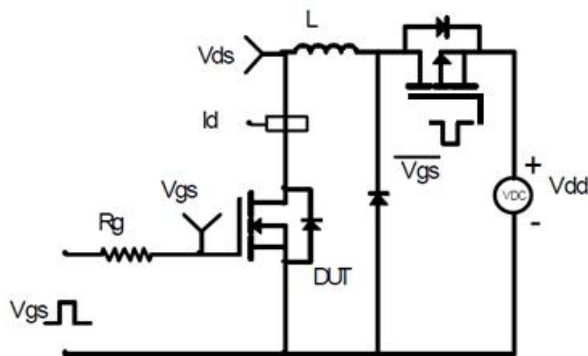
Figure 10.2 Power Dissipation vs. Temperature
TO-220MF



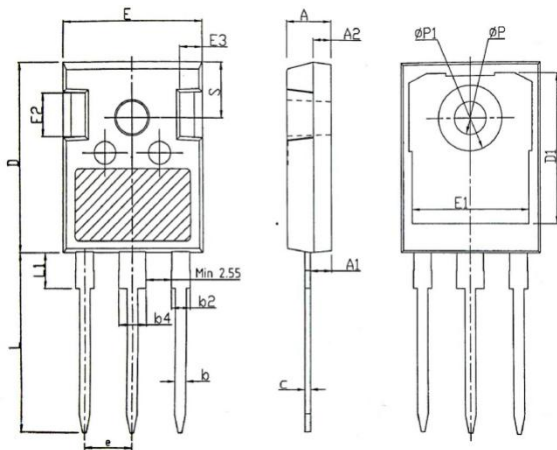
Gate Charge Test Circuit & Waveform



Unclamped Inductive Switching Test Circuit & Waveforms

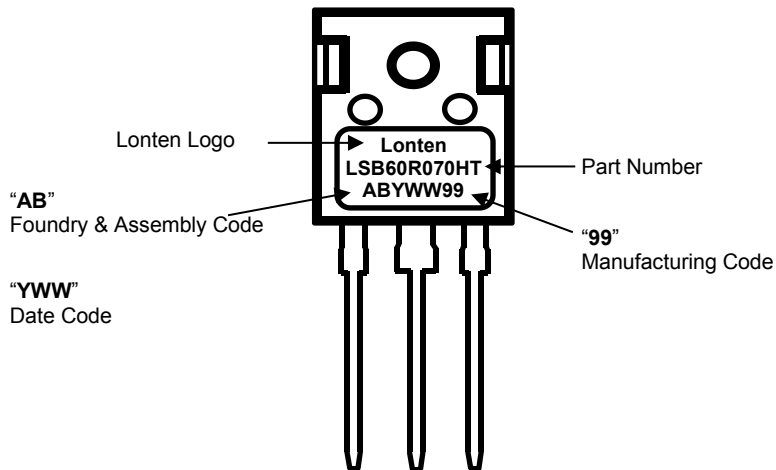


Mechanical Dimensions for TO-247

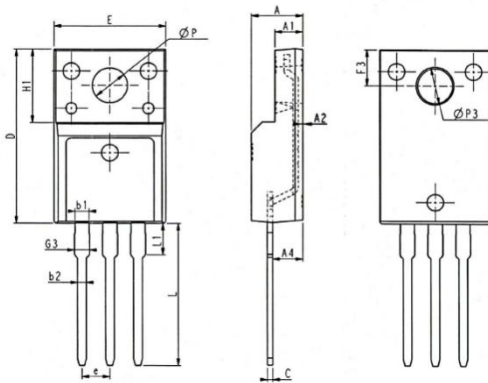


| SYMBOL | mm | | |
|--------|---------|-------|-------|
| | MIN | NOM | MAX |
| A | 4.80 | 5.00 | 5.20 |
| A1 | 2.21 | 2.41 | 2.59 |
| A2 | 1.85 | 2.00 | 2.15 |
| b | 1.11 | 1.21 | 1.36 |
| b2 | 1.91 | 2.01 | 2.21 |
| b4 | 2.91 | 3.01 | 3.21 |
| c | 0.51 | 0.61 | 0.75 |
| D | 20.80 | 21.00 | 21.30 |
| D1 | 16.25 | 16.55 | 16.85 |
| E | 15.50 | 15.80 | 16.10 |
| E1 | 13.00 | 13.30 | 13.60 |
| E2 | 4.80 | 5.00 | 5.20 |
| E3 | 2.30 | 2.50 | 2.70 |
| e | 5.44BSC | | |
| L | 19.82 | 19.92 | 20.22 |
| L1 | — | — | 4.30 |
| ØP | 3.40 | 3.60 | 3.80 |
| ØP1 | — | — | 7.30 |
| S | 6.15BSC | | |

TO-247 Part Marking Information

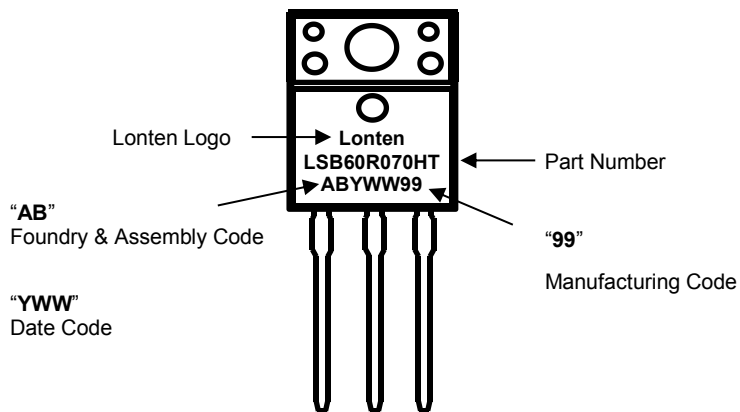


Mechanical Dimensions for TO-220MF



| SYMBOL | COMMON DIMENSIONS | | | | | |
|--------|-------------------|-------|-------|----------|-------|-------|
| | MM | | | INCH | | |
| | MIN | NOM | MAX | MIN | NOM | MAX |
| E | 9.96 | 10.16 | 10.36 | 0.392 | 0.400 | 0.408 |
| A | 4.50 | 4.70 | 4.90 | 0.177 | 0.185 | 0.193 |
| A1 | 2.34 | 2.54 | 2.74 | 0.092 | 0.100 | 0.108 |
| A2 | 0.30 | 0.45 | 0.60 | 0.012 | 0.020 | 0.024 |
| A4 | 2.65 | 2.76 | 2.96 | 0.104 | 0.109 | 0.117 |
| C | 0.40 | 0.50 | 0.65 | 0.016 | 0.020 | 0.026 |
| D | 15.57 | 15.87 | 16.17 | 0.613 | 0.625 | 0.637 |
| H1 | 6.70REF | | | 0.264REF | | |
| e | 2.54BSC | | | 0.1BSC | | |
| ØP | 3.03 | 3.18 | 3.38 | 0.119 | 0.125 | 0.133 |
| L | 12.68 | 12.98 | 13.28 | 0.499 | 0.511 | 0.523 |
| L1 | 2.88 | 3.03 | 3.18 | 0.113 | 0.119 | 0.125 |
| ØP3 | 3.15REF | | | 0.124REF | | |
| F3 | 3.15 | 3.30 | 3.45 | 0.124 | 0.130 | 0.136 |
| G3 | 1.25 | 1.35 | 1.55 | 0.049 | 0.053 | 0.061 |
| b1 | 1.18 | 1.28 | 1.43 | 0.046 | 0.050 | 0.056 |
| b2 | 0.70 | 0.80 | 0.95 | 0.028 | 0.031 | 0.037 |

TO-220MF Part Marking Information



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